

LD68I6S-A/B/C

InGaAlP Laser Diode

Quantum Semiconductor International Co., Ltd

2004. Rev 1.

◆ OVERVIEW

LD68I6S-A/B/C is a MOCVD grown 0.68 μ m band *InGaAlP* laser diode with quantum well structure. It's an attractive light source, with a typical light output power of 30mW for opto-electronic devices such as Industrials.

◆ APPLICATION

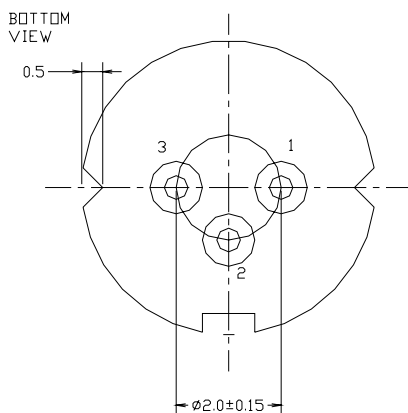
- Industrials
- Laser Module

◆ FEATURES

- Visible Light Output : $\lambda_p = 685\text{nm}$
- Optical Power Output : 30 mW CW
- Package Type : TO-18 (5.6mm ϕ)
- Built-in Photo Diode for Monitoring Laser Output

◆ ELECTRICAL CONNECTION

Bottom View



Pin Configuration

A	LD cathod, PD anode (Fig. 1)
B	LD , PD anode (Fig. 2)
C	LD anode, PD cathod (Fig. 3)

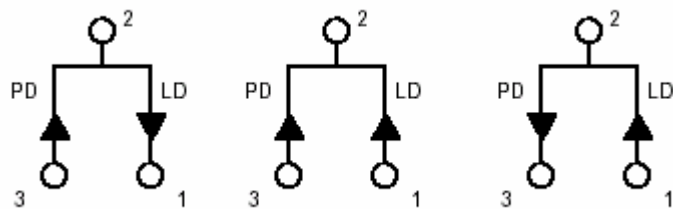


Fig. 1

LD68I6SA

Fig. 2

LD68I6SB

Fig. 3

LD68I6SC

◆ **ABSOLUTE MAXIMUM RATING at Tc=25°C**

Items	Symbols	Values	Unit
Optical Output Power	P	35	mW
Laser Diode Reverse Voltage	V	2	V
Photo Diode Reverse Voltage	V	30	V
Operating Temperature	Topr	-10 ~ +60	°C
Storage Temperature	Tstg	-40 ~ +85	°C

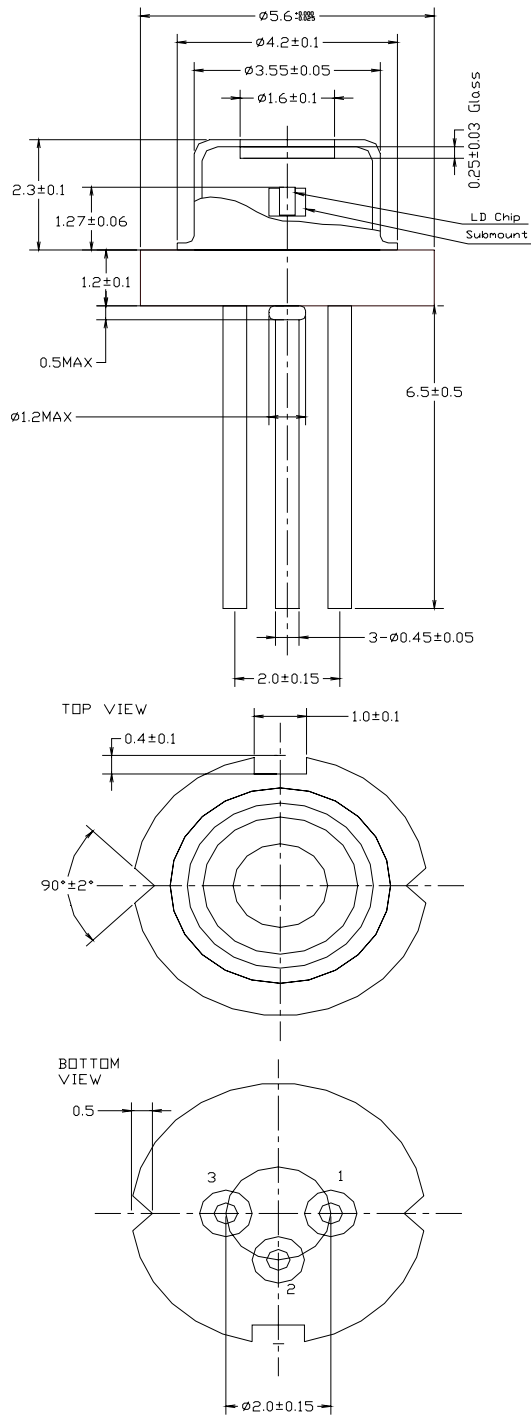
◆ **ELECTRICAL and OPTICAL CHARACTERISTICS at Tc=25°C**

Items	Symbols	Min.	Typ.	Max.	Unit	Condition
Optical Output Power	Po	-	30	-	mW	-
Threshold Current	Ith	-	35	60	mA	-
Operating Current	Iop	-	80	140	mA	Po=30mW
Operating Voltage	Vop	2	2.4	3	V	Po=30mW
Lasing Wavelength	λp	670	685	700	nm	Po=30mW
Beam Divergence	$\theta \parallel$	7	9.5	12	deg	Po=30mW
	$\theta \perp$	16	20	25	deg	Po=30mW
Beam Angle	$\Delta \theta \parallel$	-	-	± 2.0	deg	Po=30mW
	$\Delta \theta \perp$	-	-	± 2.5	deg	Po=30mW
Monitor Current	Im	0.05	0.2	2.5	mA	Po=30mW
Astigmatism	As	-	-	8	μm	
Optical Distance	$\Delta X, \Delta Y, \Delta Z$	-	-	± 60	μm	

NOTICE : LD68I6S-A/B/C to be operated on APC circuit

The above product specification are subject to change without notice.

◆ PACKAGE DIMENSION



◆ PACKING

